

Please amend Claim 18 as follows:

A¹

1 18. (once amended) An integrated circuit comprising:
2 a semiconductor substrate;
3 a first drain region disposed in said substrate;
4 a first channel region disposed in said substrate directly adjacent to said
5 first drain region;
6 a first gate dielectric overlying said first channel region;
7 a first gate overlying said first gate dielectric;
8 a first source region disposed in said substrate directly adjacent to said
9 first channel region;
10 a second channel region disposed in said substrate directly adjacent to
11 said first source region and on a side of said first source region opposite to said
12 first channel region;
13 a second gate dielectric overlying said second channel region;
14 a second gate overlying said second gate dielectric;
15 a second drain region disposed in said substrate directly adjacent to said
16 second channel region; and
17 an input/output pad electrically coupled to said first gate and to said
18 second drain region.

Please cancel ~~Claims~~ Claims 19 – 21.

Please amend Claim 22 as follows:

A2

1 22. (once amended) A method of forming an integrated circuit, said
2 method comprising:
3 forming a first drain region in a semiconductor substrate;
4 forming a first source region in said substrate separated from said first
5 drain region solely by a first channel region;
6 forming a second drain region in said substrate separated from said first
7 source region solely by a second channel region, wherein said second channel
8 region is a different region than said first channel region;
9 forming a first gate dielectric overlying said first channel region and a
10 second gate dielectric overlying said second channel region;
11 forming a first gate overlying said first gate dielectric and a second gate
12 overlying said second gate dielectric; and
13 forming an input/output pad on said semiconductor substrate electrically
14 coupled to said first gate and to said second drain region.

Please ~~cancel~~ Claims 23 and 24.

REMARKS

Reconsideration of the above-identified Application is respectfully requested. Claims 1-24 are in the case. Claims 17, 19 – 21, 23 and 24 have been canceled. Claims 18 and 22 have been amended.

Applicants acknowledge with appreciation the allowance of Claims 1 – 16.